**Product data sheet** 

## 1. General description

Hyperfast power diode in a 2-lead TO220 plastic package.





### 2. Features and benefits

- Low leakage current
- · Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

# 3. Applications

- · Active PFC in air conditioner/EV charger/PV
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			650			V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; square-wave pulse; $T_{mb} \le 127$ °C; Fig. 1; Fig. 2; Fig. 3		8			Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb} \le$ 127 °C; square-wave pulse		16			Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		91		Α	
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		100		Α	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.20	3.20	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.45	2.45	V
Dynamic	characteristics				,		
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	13	-	ns

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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	5 0 7	1/ 1/1 A
2	Α	anode	Ţ ŲŢ	K <del>   </del> A 001aaa020
mb	mb	mounting base; connected to cathod		

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC8M-650P	TO220-2L	BYC8M-650PQ	Tube	50	TO220d-2L	13-Oct-2022

# 7. Marking

#### Table 4. Marking codes

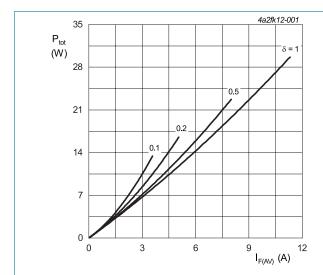
Type number	Marking codes
BYC8M-650P	BYC8M 650P

# 8. Limiting values

### **Table 5. Limiting values**

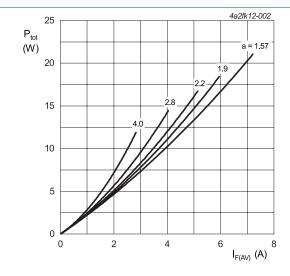
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			650	V
$V_{RWM}$	crest working reverse voltage			650	V
$V_R$	reverse voltage	DC		650	V
I <sub>F(AV)</sub>	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 127$ °C; Fig. 1; Fig. 2; Fig. 3		8	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 127 °C; square-wave pulse		16	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		91	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		100	Α
T <sub>stg</sub>	storage temperature			-65 to 175	°C
T <sub>j</sub>	junction temperature			-65 to 175	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 2.097 \text{ V; } R_s = 0.0464 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



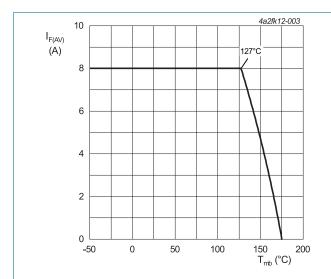
a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 2.097 V;  $R_s$  = 0.0464  $\Omega$ 

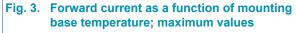
Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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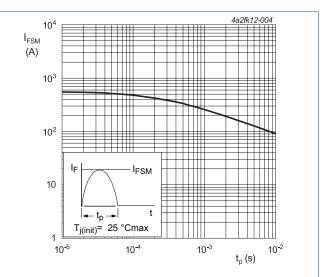


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5		-	-	2.1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

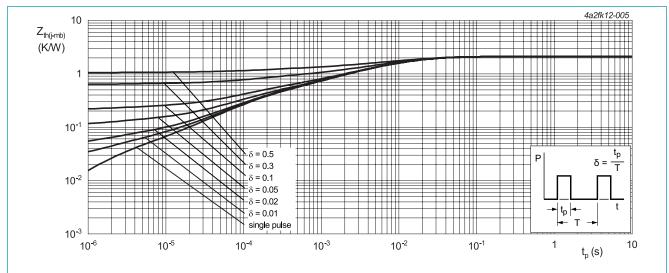
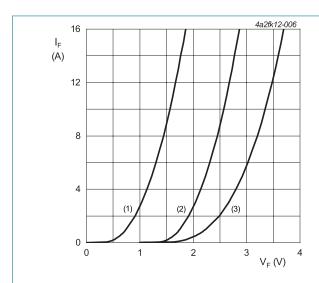


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
$V_{F}$	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.20	3.20	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.45	2.45	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.6	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	0.07	0.8	mA
Dynamic	characteristics						
Q <sub>r</sub>	reverse charge	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	38	-	nC
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	93	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{rr} = 0.25 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	20	-	ns
		$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	13	-	ns
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	28	-	ns
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	45	-	ns
I <sub>RM</sub>	peak reverse recovery currentnon-repetitive avalanche energy	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	2.7	-	А
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	4.2	-	А
E <sub>as</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C		10.8	-	-	mJ



 $V_0 = 2.097 \text{ V}; R_s = 0.0464 \Omega$ 

(1) T<sub>i</sub> = 150 °C; typical values

(2) T<sub>i</sub> = 150 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values



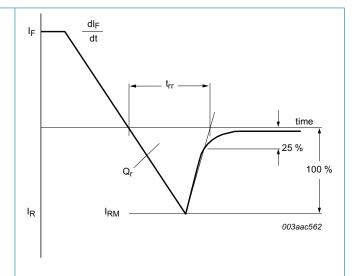
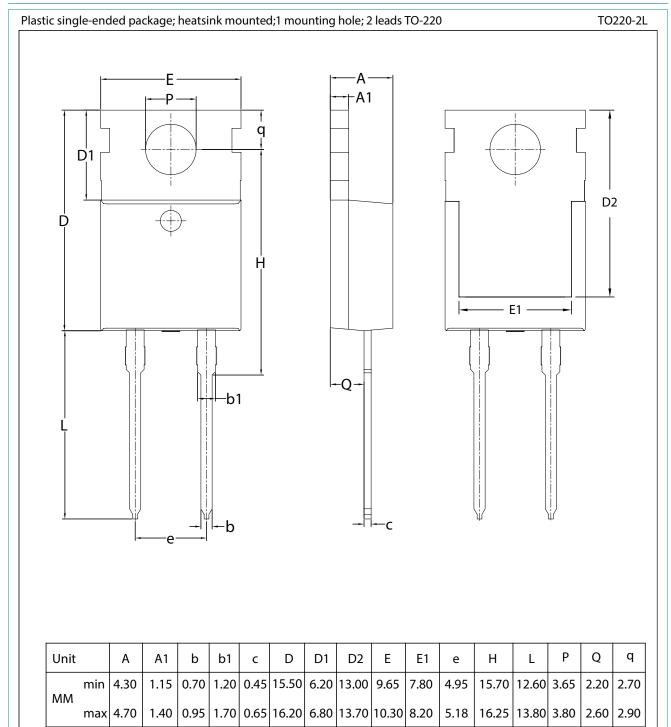


Fig. 7. Reverse recovery definitions; ramp recovery

# 11. Package outline



#### Note:

1. All dimensions don't include mold flash and metal protrusion.

#### Hyperfast power diode

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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